



# PJM50P40DN

## P-Channel Enhancement Mode Power MOSFET

### Product Summary

- $V_{DS} = -40V, I_D = -50A$
- $R_{DS(on)} < 11.5m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 17.5m\Omega @ V_{GS} = -4.5V$

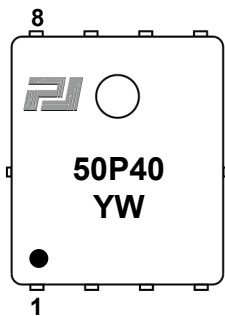
### Features

- Advanced Trench Technology
- 100% Avalanche Tested
- RoHS Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

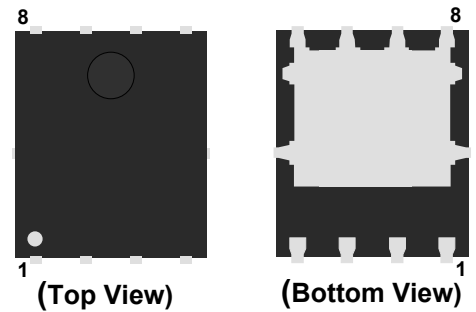
### Application

- Battery Protection
- Load Switch
- Uninterruptible power supply

### Marking Code

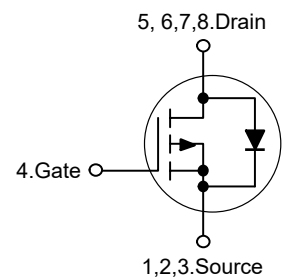


### PDFN5x6-8L



| Pin     | Description |
|---------|-------------|
| 1,2,3   | Source      |
| 4       | Gate        |
| 5,6,7,8 | Drain       |

### Schematic Diagram



### Absolute Maximum Ratings

Ratings at 25°C case temperature unless otherwise specified.

| Parameter                                      | Symbol    | Value       | Unit |
|------------------------------------------------|-----------|-------------|------|
| Drain-Source Voltage                           | $-V_{DS}$ | 40          | V    |
| Gate-Source Voltage                            | $V_{GS}$  | $\pm 20$    | V    |
| Drain Current-Continuous                       | $-I_D$    | 50          | A    |
| Drain Current-Pulsed <sup>Note1</sup>          | $-I_{DM}$ | 160         | A    |
| Maximum Power Dissipation                      | $P_D$     | 52          | W    |
| Single Pulse Avalanche Energy <sup>Note2</sup> | $E_{AS}$  | 90          | mJ   |
| Junction Temperature                           | $T_J$     | 150         | °C   |
| Storage Temperature Range                      | $T_{STG}$ | -55 to +150 | °C   |

### Thermal Characteristics

|                                      |                 |     |      |
|--------------------------------------|-----------------|-----|------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.4 | °C/W |
|--------------------------------------|-----------------|-----|------|



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### Electrical Characteristics

(T<sub>J</sub>=25°C unless otherwise specified)

| Parameter                                   | Symbol                | Test Condition                                                                                | Min. | Typ. | Max. | Unit |
|---------------------------------------------|-----------------------|-----------------------------------------------------------------------------------------------|------|------|------|------|
| Static Characteristics                      |                       |                                                                                               |      |      |      |      |
| Drain-Source Breakdown Voltage              | -V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA                                                   | 40   | --   | --   | V    |
| Zero Gate Voltage Drain Current             | -I <sub>DSS</sub>     | V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V                                                    | --   | --   | 1    | μA   |
| Gate-Body Leakage Current                   | I <sub>GSS</sub>      | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                                    | --   | --   | ±100 | nA   |
| Gate Threshold Voltage <sup>Note3</sup>     | -V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA                                     | 1    | 1.6  | 2.5  | V    |
| Drain-Source On-Resistance <sup>Note3</sup> | R <sub>DS(on)</sub>   | V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A                                                   | --   | --   | 11.5 | mΩ   |
|                                             |                       | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A                                                  | --   | --   | 17.5 | mΩ   |
| Dynamic Characteristics                     |                       |                                                                                               |      |      |      |      |
| Input Capacitance                           | C <sub>iss</sub>      | V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, f=1MHz                                            | --   | 1997 | --   | pF   |
| Output Capacitance                          | C <sub>oss</sub>      |                                                                                               | --   | 258  | --   | pF   |
| Reverse Transfer Capacitance                | C <sub>rss</sub>      |                                                                                               | --   | 205  | --   | pF   |
| Total Gate Charge                           | Q <sub>g</sub>        | V <sub>DS</sub> =-20V, I <sub>D</sub> =-10A<br>, V <sub>GS</sub> =-10V                        | --   | 35   | --   | nC   |
| Gate-Source Charge                          | Q <sub>gs</sub>       |                                                                                               | --   | 6.2  | --   | nC   |
| Gate-Drain Charge                           | Q <sub>gd</sub>       |                                                                                               | --   | 7.3  | --   | nC   |
| Switching Characteristics                   |                       |                                                                                               |      |      |      |      |
| Turn-on Delay Time                          | t <sub>d(on)</sub>    | V <sub>DD</sub> =-20V, I <sub>D</sub> =-10A,<br>V <sub>GS</sub> =-10V, R <sub>GEN</sub> =2.5Ω | --   | 10   | --   | nS   |
| Turn-on Rise Time                           | t <sub>r</sub>        |                                                                                               | --   | 20   | --   | nS   |
| Turn-off Delay Time                         | t <sub>d(off)</sub>   |                                                                                               | --   | 51   | --   | nS   |
| Turn-off Fall Time                          | t <sub>f</sub>        |                                                                                               | --   | 28   | --   | nS   |
| Source-Drain Diode Characteristics          |                       |                                                                                               |      |      |      |      |
| Diode Forward Voltage <sup>Note3</sup>      | -V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =-10A                                                     | --   | --   | 1.2  | V    |
| Diode Forward Current                       | -I <sub>S</sub>       |                                                                                               | --   | --   | 50   | A    |

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. E<sub>AS</sub> Condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=-20V, V<sub>G</sub>=-10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=-19A.

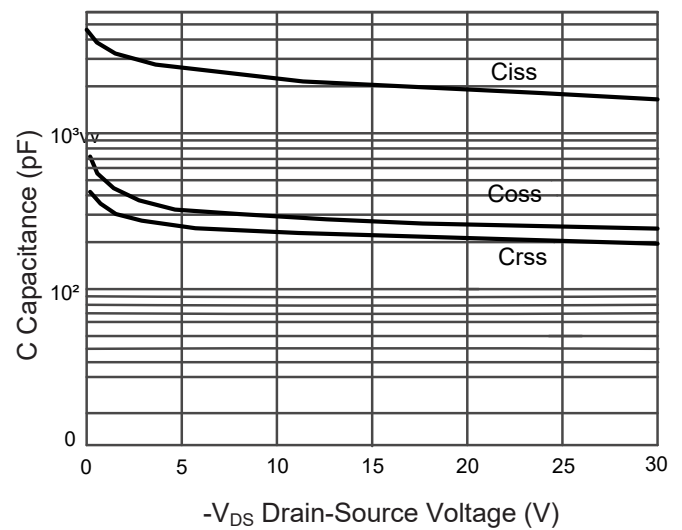
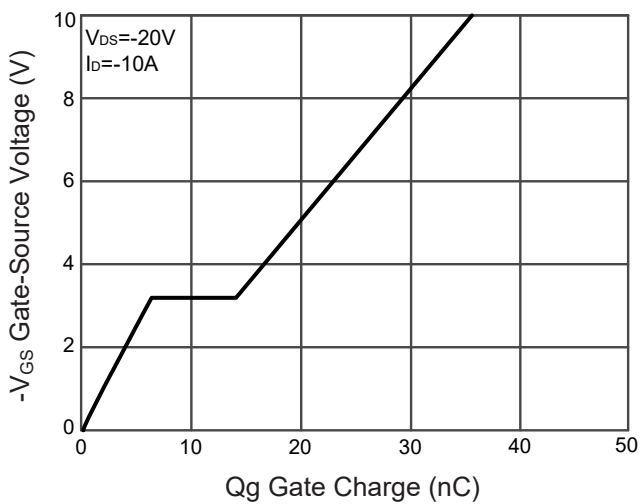
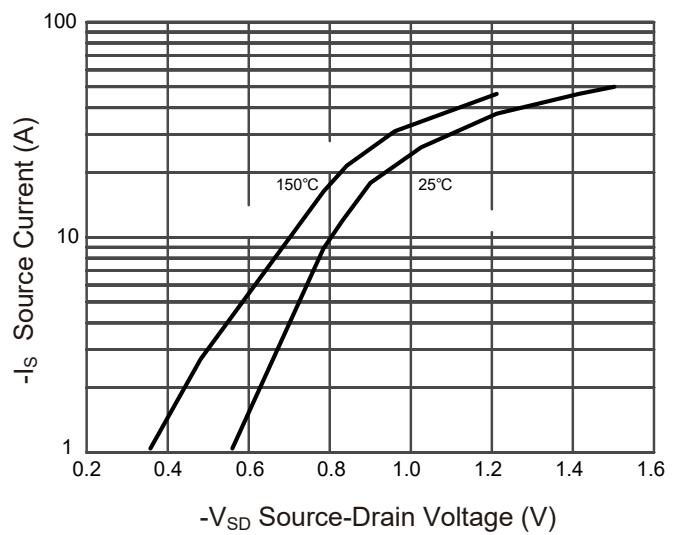
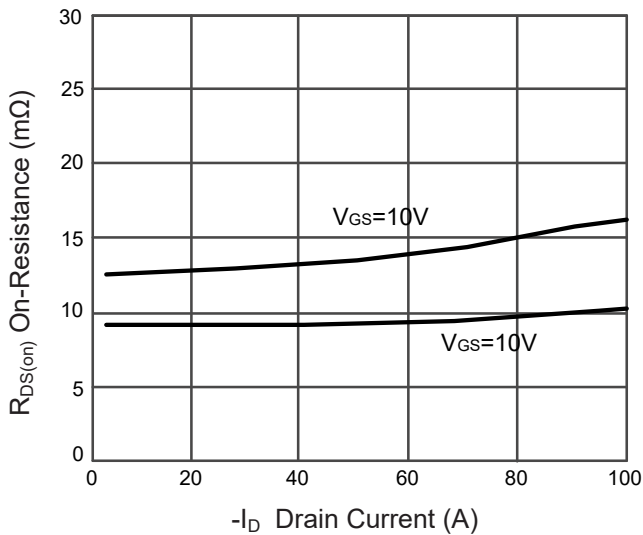
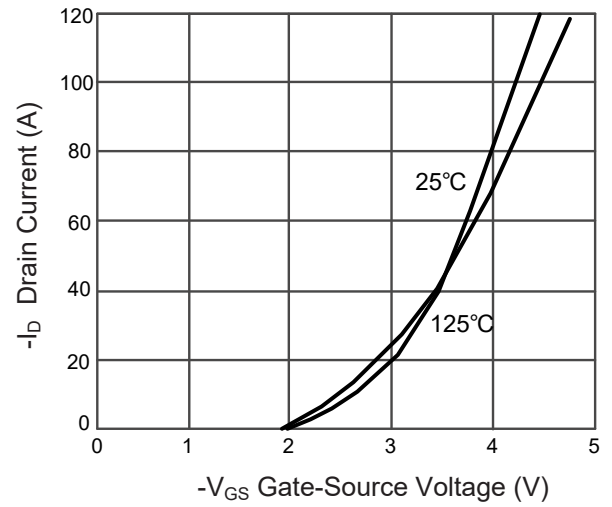
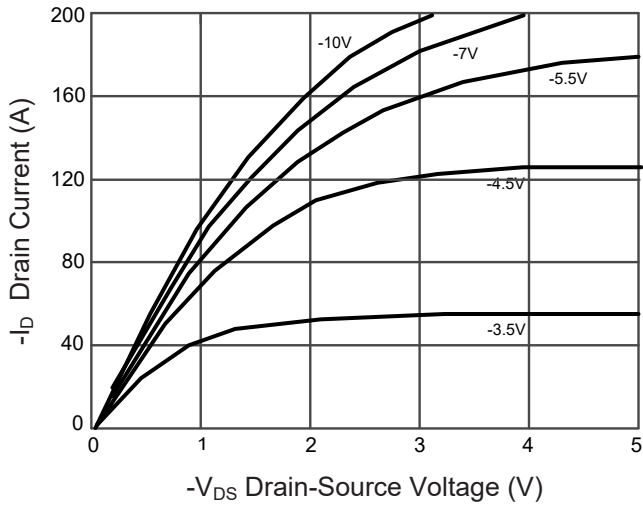
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.



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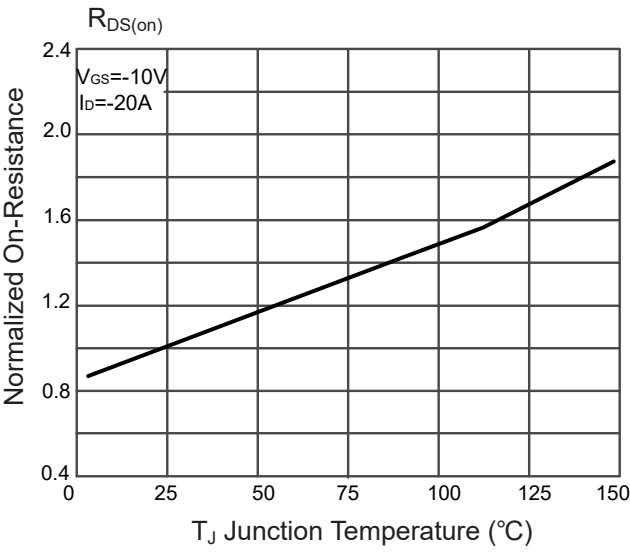
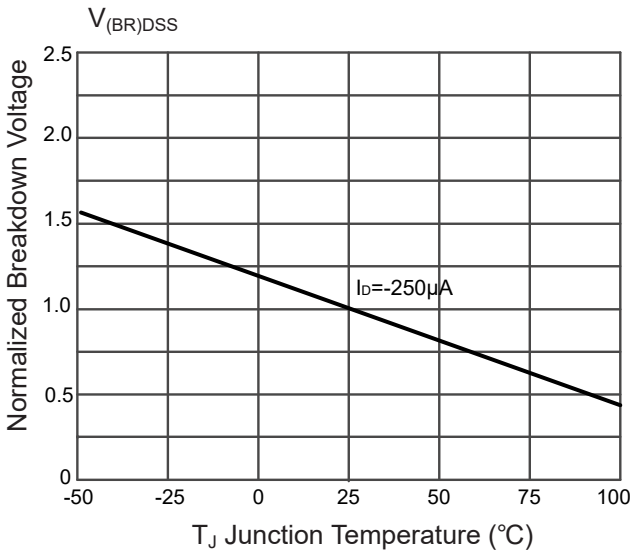
### Typical Characteristic Curves





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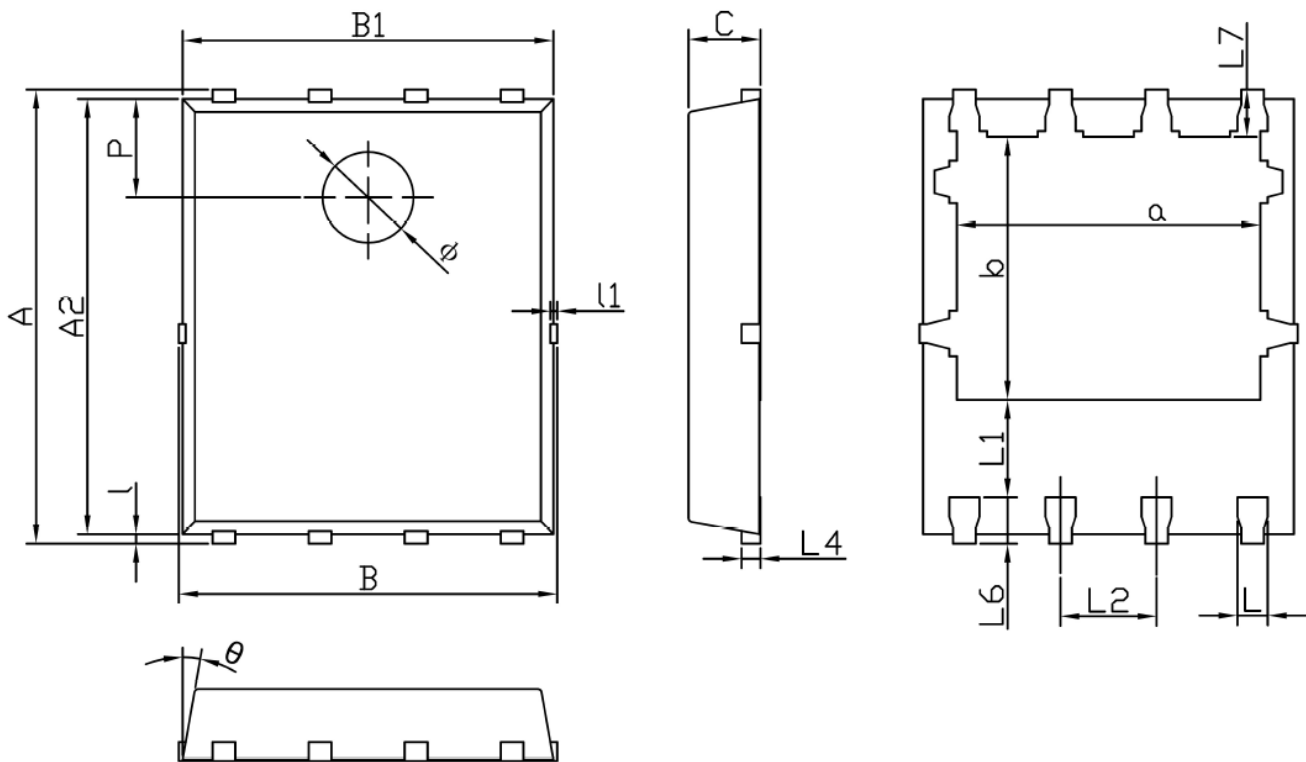


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### Package Outline

PDFN5x6-8L  
Dimensions in mm



| Symbol | Dimensions |       | Symbol   | Dimensions |      |
|--------|------------|-------|----------|------------|------|
|        | Min.       | Max.  |          | Min.       | Max. |
| A      | 5.90       | 6.10  | L1       | 1.10       | -    |
| a      | 3.91       | 4.11  | l1       | -          | 0.10 |
| A2     | 5.70       | 5.80  | L2       | 1.17       | 1.37 |
| B      | 4.90       | 5.10  | L4       | 0.21       | 0.34 |
| b      | 3.375      | 3.575 | L6       | 0.51       | 0.71 |
| B1     | 4.80       | 5.00  | L7       | 0.51       | 0.71 |
| C      | 0.90       | 1.00  | P        | 1.15       | 1.45 |
| L      | 0.30       | 0.50  | $\theta$ | 8°         | 12°  |
| I      | 0.06       | 0.20  | $\Phi$   | 1.10       | 1.30 |